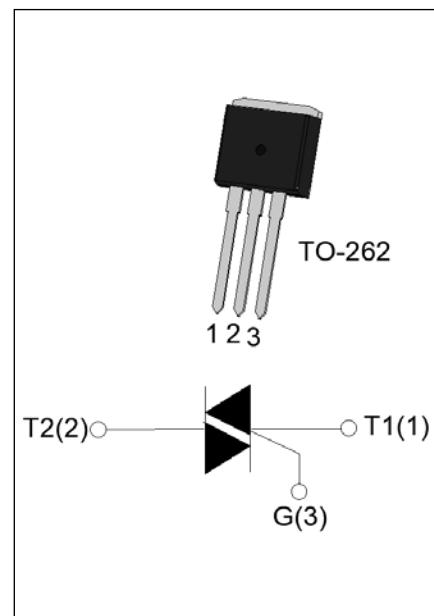


**DESCRIPTION:**

The JST139D-800E triac is suitable for general purpose AC switching. It can be used as an ON/OFF function in applications such as heating regulation, induction motor starting circuits, for phase control operation in light dimmers, motor speed controllers. From T2 terminals to external heatsink. Package TO-262 is RoHS compliant.

**MAIN FEATURES**

Symbol	Value	Unit
$I_{T(\text{RMS})}$	16	A
$V_{\text{DRM}} / V_{\text{RRM}}$	800	V
$I_{G(T_{I/II/III/IV})}$	10/10/10/25	mA

**ABSOLUTE MAXIMUM RATINGS**

Parameter	Symbol	Value	Unit
Storage junction temperature range	$T_{\text{stg}}$	-40-150	°C
Operating junction temperature range	$T_j$	-40-125	°C
Repetitive peak off-state voltage ( $T_j=25^\circ\text{C}$ )	$V_{\text{DRM}}$	800	V
Repetitive peak reverse voltage ( $T_j=25^\circ\text{C}$ )	$V_{\text{RRM}}$	800	V
RMS on-state current ( $T_c \leqslant 95^\circ\text{C}$ )	$I_{T(\text{RMS})}$	16	A
Non repetitive surge peak on-state current (full cycle , $t_p=20\text{ms}$ , $T_j=25^\circ\text{C}$ )	$I_{\text{TSM}}$	140	A
Non repetitive surge peak on-state current (full cycle , $t_p=16.6\text{ms}$ , $T_j=25^\circ\text{C}$ )		154	
$I^2t$ value for fusing ( $t_p=10\text{ms}$ , $T_j=25^\circ\text{C}$ )	$I^2t$	98	$\text{A}^2\text{s}$
Critical rate of rise of on-state current ( $I_G=2 \times I_{GT}$ , $f=100\text{Hz}$ , $T_j=125^\circ\text{C}$ )	I - II III-IV	80 50	$\text{A}/\mu\text{s}$
Peak gate current ( $t_p=20\mu\text{s}$ , $T_j=125^\circ\text{C}$ )	$I_{GM}$	4	
Average gate power dissipation ( $T_j=125^\circ\text{C}$ )	$P_{G(\text{AV})}$	0.5	W
Peak gate power	$P_{GM}$	10	W
Peak pulse voltage ( $T_j=25^\circ\text{C}$ ; non-repetitive,off-state;FIG.7)	$V_{pp}$	4.5	kV

ELECTRICAL CHARACTERISTICS ( $T_j=25^\circ\text{C}$  unless otherwise specified)

Symbol	Test Condition	Quadrant	Value		Unit
$I_{GT}$	$V_D=12\text{V}$ $R_L=33\Omega$	I - II -III	MAX.	10	mA
		IV		25	
$V_{GT}$	ALL		MAX.	1	V
$V_{GD}$	$V_D=V_{DRM}$ $T_j=125^\circ\text{C}$ $R_L=3.3\text{K}\Omega$	ALL	MIN.	0.2	V
$I_L$	$I_G=1.2I_{GT}$	I - III - IV	MAX.	25	mA
		II		35	
$I_H$	$I_T=500\text{mA}$		MAX.	25	mA
$dV/dt$	$V_D=540\text{V}$ Gate Open $T_j=125^\circ\text{C}$		MIN.	100	V/ $\mu\text{s}$
$(dV/dt)c$	$(dI/dt)c=7.2\text{A/ms}$ , $T_j=110^\circ\text{C}$		MIN.	5	V/ $\mu\text{s}$
$t_{on}$	$I_G=40\text{mA}$ $I_A=200\text{mA}$ $I_R=20\text{mA}$ $T_j=25^\circ\text{C}$	TYP.	3	$\mu\text{s}$	
			50		

## STATIC CHARACTERISTICS

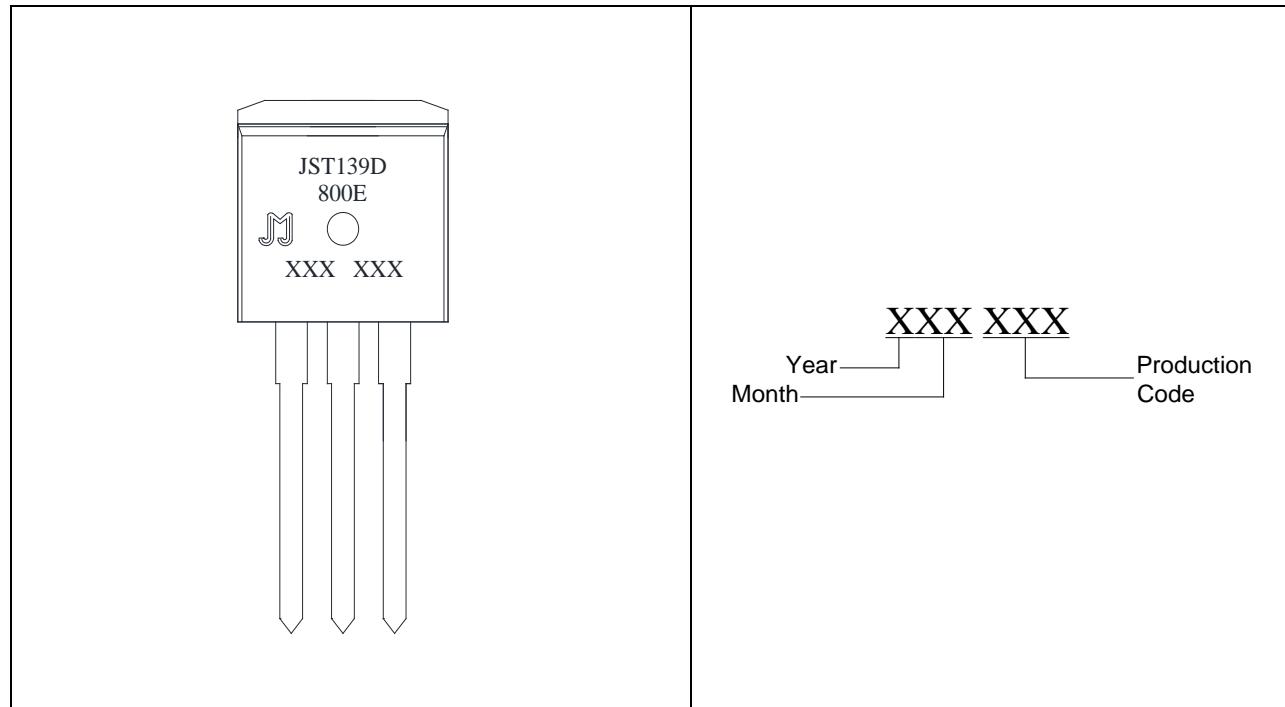
Symbol	Parameter		Value(MAX.)	Unit
$V_{TM}$	$I_{TM}=15\text{A}$	$t_p=380\mu\text{s}$	$T_j=25^\circ\text{C}$	1.5 V
$V_{TO}$	Threshold voltage		$T_j=125^\circ\text{C}$	0.75 V
$R_D$	Dynamic resistance		$T_j=125^\circ\text{C}$	27 m $\Omega$
$I_{DRM}$	$V_D=V_{DRM}$ $V_R=V_{RRM}$	$T_j=25^\circ\text{C}$	5 $\mu\text{A}$	$\mu\text{A}$
$I_{RRM}$			$T_j=125^\circ\text{C}$	

## THERMAL RESISTANCES

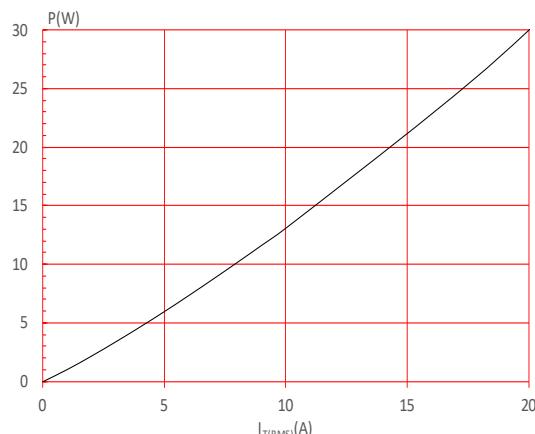
Symbol	Parameter	Value	Unit
$R_{th(j-c)}$	junction to case (AC)	1.3	°C/W
$R_{th(j-a)}$	junction to ambient (AC)	60	°C/W

**ORDERING INFORMATION**

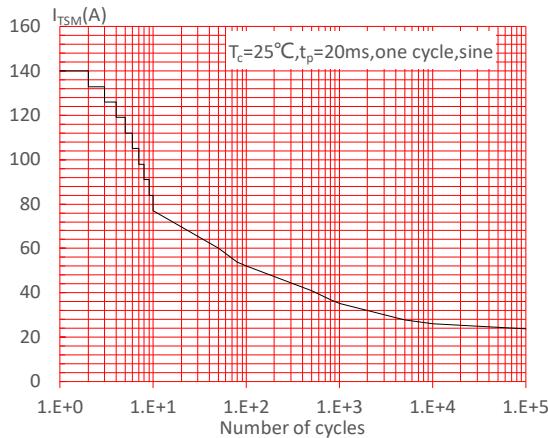
<b>J</b>	<b>ST</b>	<b>139</b>	<b>D</b>	<b>-800</b>	<b>E</b>
JieJie Microelectronics Co., Ltd.					
	Triacs				
		I <sub>T(RMS)</sub> :16A			
			D:TO-262		
				800:V <sub>DRM</sub> /V <sub>RRM</sub> ≥800V	
					E:I <sub>GT1-3</sub> ≤10mA I <sub>GT4</sub> ≤25mA

**MARKING**

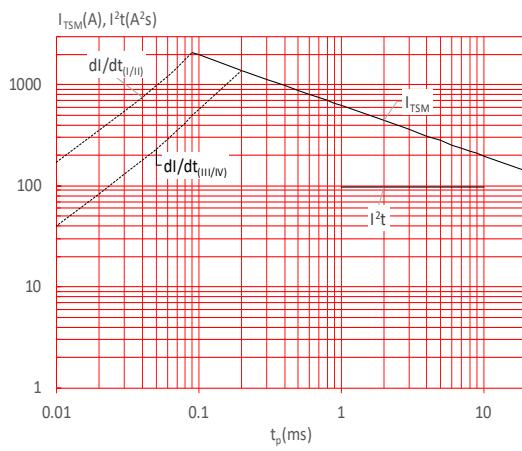
**FIG.1** Maximum power dissipation versus RMS on-state current



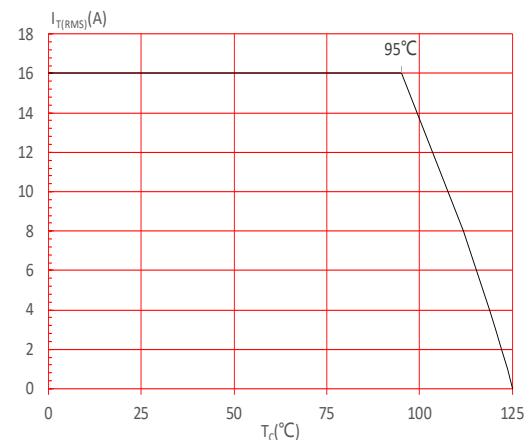
**FIG.3:** Surge peak on-state current versus number of cycles



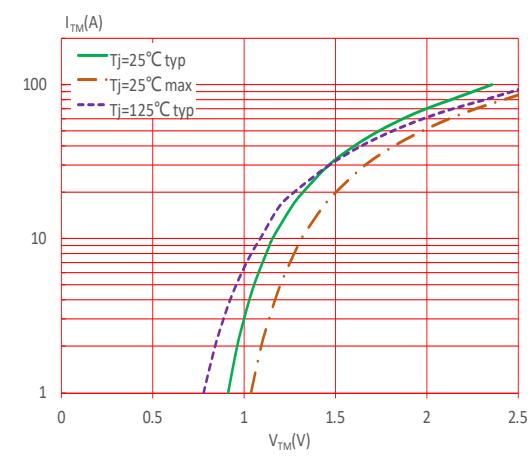
**FIG.5:** Non-repetitive surge peak on-state current for a sinusoidal pulse with width  $t_p < 20\text{ms}$ , and corresponding value of  $I^2t$   
( I - II :  $dl/dt < 80\text{A}/\mu\text{s}$ ; III - IV :  $dl/dt < 50\text{A}/\mu\text{s}$ )



**FIG.2:** RMS on-state current versus case temperature



**FIG.4:** On-state characteristics



**FIG.6:** Relative variations of gate trigger current, holding current and latching current versus junction temperature

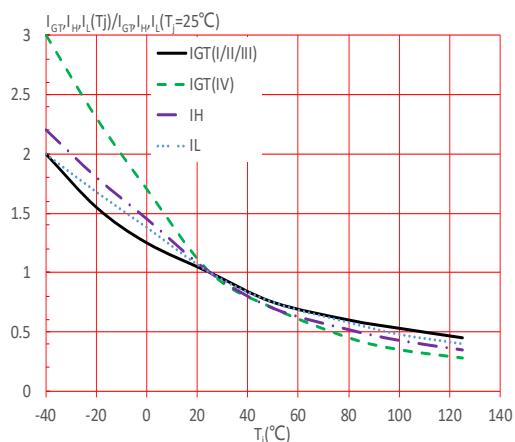
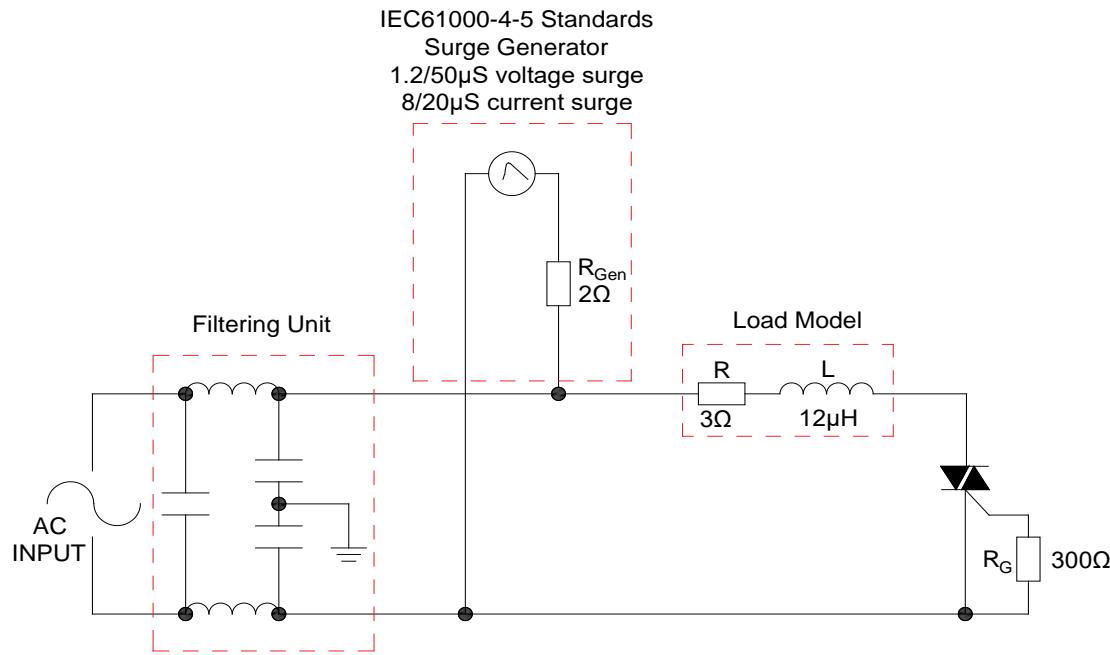


FIG.7: Test circuit for inductive and resistive loads to IEC-61000-4-5 standards



## SHAPING AND SOLDERING PARAMETERS

Refer to 《Instructions for installation of plastic-sealed in-line power devices》 released by JieJie.

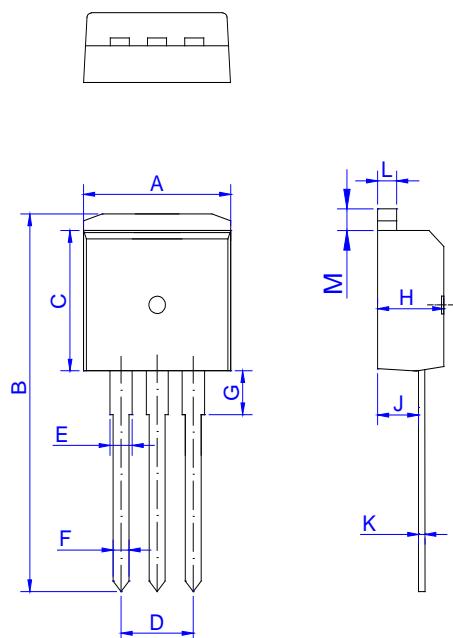
**ORDERING INFORMATION**

Order code	Voltage $V_{DRM}/V_{RRM}$ (V)	IGT(mA)		Package	Base qty. (pcs)	Delivery mode
		I - II - III	IV			
<b>JST139D-800E</b>	<b>800</b>	<b>10</b>	<b>25</b>	<b>TO-262</b>	<b>50</b>	<b>Tube</b>

**Document Revision History**

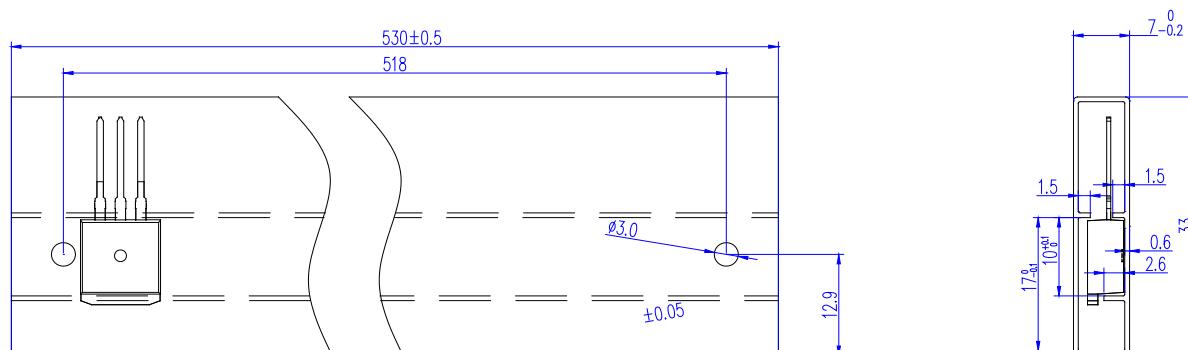
Date	Revision	Changes
Apr.14, 2023	A.1.0	Last updated

## PACKAGE MECHANICAL DATA



Ref.	Dimensions					
	Millimeters			Inches		
	Min.	Typ.	Max.	Min.	Typ.	Max.
A	9.95		10.20	0.392		0.402
B	23.85		24.05	0.939		0.947
C	9.40		9.60	0.370		0.378
D	4.95		5.25	0.195		0.207
E	1.35		1.40	0.053		0.055
F	0.80		0.85	0.031		0.033
G	2.70		3.40	0.106		0.134
H	4.45		4.55	0.175		0.179
J	2.20		2.60	0.087		0.102
K	0.48		0.52	0.019		0.020
L	1.30		1.35	0.051		0.053
M	1.20		1.50	0.047		0.059

## DELIVERY MODE



PACKAGE	OUTLINE	TUBE (PCS)	INNER BOX (PCS)	PER CARTON
TO-262	TUBE	50	1,000	5,000

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